

UTC D65H2 PNP EXPITAXIAL SILICON TRANSISTOR

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DESCRIPTION

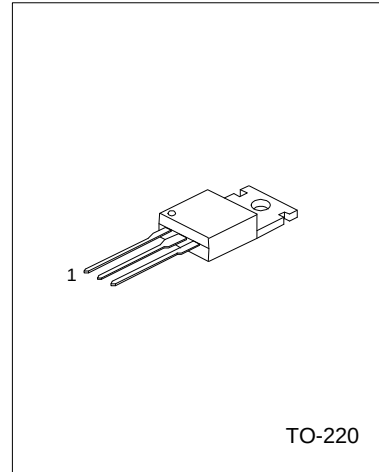
The UTC D65H2 is a general purpose power application and switching.

FEATURE

*Low Collector-Emitter Saturation Voltage

VCE(sat)=-1v(MAX)@-15A

*Fast Switching Speeds



1:BASE 2:COLLECTOR 3:EMITTER

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

PARAMETER	SYMBOL	VALUE	UNIT
Collector to Emitter Voltage	VCEO	-30	V
Emitter To Base Voltage	VEBO	-5	V
Collector Current(DC)	IC	-15	A
Collector Current(Pulse)	IC	-25	A
Collector Dissipation(Tc=25°C)	Pc	50	W
Collector Dissipation(Ta=25°C)	Pc	1.67	W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55 ~ +150	°C

*PW<=10mS,Duty Cycle<=50%

ELECTRICAL CHARACTERISTICS(Ta=25°C)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector Cutoff Current	ICES	VCE=Rated ; VCEO,VEB=0			-10	μA
Emitter Cutoff current	IEBO	VEB=-5V,IC=0			-10	μA
Collector Emitter Saturation Voltage	VCE(SAT)	IC=-10A,IB=-0.1A			0.6	V
Base Emitter Saturation Voltage	VBE(SAT)	IC=-10A,IB=-1A			-1.5	V
DC Current Gain	hFE1	IC=-10A,VCE=-1V	100			
Current Gain Bandwidth Product	FT	VCE=-10V,IC=-0.5A		40		MHZ
Output Capacitance	CCB	VCB=-10V,f=1MHZ		350		PF
Turn On Time	ton	IC=-5A,IB=-0.5A		150		nS
Storage Time	tstg	IB=-0.5A		600		nS
Fall Time	tf			120		nS